

G. Device & Process Modeling, Simulation and Reliability 분과

Room G

하나스퀘어 (B112)

일 시 : 2월 17일(금) 09:30-11:00

세션명 : [FG1-G] Modeling and Simulation I

좌 장 : 이성현(한국외국어대학교), 신민철(KAIST)

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- FG1-G-1 09:30-10:00 **[Invited]** Tunneling Field-Effect Transistors: The Next-Generation Devices
저자: Woo Young Choi
소속: Department of Electronic Engineering, Sogang University
- FG1-G-2 10:00-10:15 **Optimization of Gateless MOSFET (Biristor)**
저자: Seung-Won Ko, Dong-Il Moon, Sungho Kim, Ji-Min Choi, and Yang-Kyu Choi
소속: Department of Electrical Engineering, KAIST
- FG1-G-3 10:45-11:00 **Characterization of Floating-base Bipolar Junction Transistor as a 2-terminal Select Device for Cross-Point Memory Devices**
저자: Jong-Ho Bae, Chang-Hee Kim, and Jong-Ho Lee
소속: Inter-University Semiconductor Research Center (ISRC) and School of Electrical Engineering, Seoul National University
- FG1-G-4 10:15-10:30 **Transfer Characteristics Simulation for Hydrogenated Amorphous Silicon Thin Film Transistors using High Field Mobility Degradation Model**
저자: Seunghyun Jang, Jaehong Lee, Jaeho Lee, and Hyungcheol Shin
소속: Inter-University Semiconductor Research Center (ISRC) and School of Electrical Engineering, Seoul National University
- FG1-G-5 10:30-10:45 **Temperature Dependent Mobility Characteristics for the InGaZnO_x Thin Film Transistor**
저자: Sang-Ho Rha^{1,2}, Jisim Jung¹, Un Ki Kim¹, Yoon Jang Chung¹, Eun Suk Hwang¹, and Cheol Seong Hwang¹
소속: ¹Department of Materials Science and Engineering and Inter-

university Semiconductor Research Center, Seoul National
University, ²Process Development Team, Semiconductor R&D
Center, Samsung Electronics Co., Ltd.